

## IN THE CLAIMS

This listing of claims replaces all prior listings:

1. (Previously Presented) A solid-state imaging device having an imaging region section provided with a plurality of pixels and a processing circuit section for processing an image signal output from the imaging region section, the solid-state imaging device comprising:
  - each pixel having a photoelectric converting element which generates a signal charge commensurate with a light-receiving amount;
  - a charge holding region of a second conductivity type which holds a signal charge;
  - a transfer transistor which transfers a signal charge generated by the photoelectric converting element to the charge holding region and has a threshold channel potential for turning on the transfer transistor which is set to a value higher than a potential which depletes the photoelectric converting element;
  - a drain transistor which drains a signal charge generated by the photoelectric converting element and has a threshold channel potential for turning on the drain transistor which is set to a value higher than a potential which depletes the photoelectric converting element; and
  - a driver configuration unit which controls the transfer of signals in said device, wherein,
    - said driver configuration unit is configured such that after the transfer transistor simultaneously transfers the signal charge from all photoelectric converting elements to the charge holding region an exposure time of the photoelectric converting element starts while the processing unit reads the signal charge from the pixel, and
    - the photoelectric converting element comprises a buried photodiode having a charge separating region comprising a first conductivity type high-concentration impurity layer in an extreme surface of a semiconductor substrate and a charge storing region comprising a second conductivity type impurity layer in a layer beneath the charge separating region.
2. (Previously Presented) A solid-state imaging device according to claim 1, further having a reset transistor for resetting the charge holding region with a signal charge, an amplifying transistor for outputting an electric signal corresponding to a potential on the charge holding region, and a selecting transistor for selectively activating the amplifying transistor.

3. (Cancelled).

4. (Currently Amended) A solid-state imaging device according to claim 1, wherein after simultaneously resetting ~~the at least one~~ floating diffusion ~~parts~~-~~part~~ on all the pixels in the imaging region section, signal charges of the photodiodes on all the pixels are simultaneously transferred to the charge holding regions, next the signal charges transferred to the charge holding regions are read out on a pixel-row basis, to keep the drain transistor on until the reading operation proceeds to a predetermined exposure start row and drain the signal charges of the photodiodes on all the pixels, and to turn off the drain transistor when proceeded to the predetermined exposure start row and start an exposure on all the pixels.

5. (Previously Presented) A solid-state imaging device according to claim 4, wherein the photodiode, immediately after transferring the signal charge of the photodiode to the charge holding region by the transfer transistor, has remaining charges of 20 or less while the photodiode, immediately after draining the signal charge of the photodiode by the drain transistor, has remaining charges of 20 or less.

6. (Original) A solid-state imaging device according to claim 4, wherein the drain transistor being on has a gate voltage level higher than a gate voltage level of the transfer transistor being on.

7. (Original) A solid-state imaging device according to claim 4, wherein the drain transistor being on has a gate voltage level higher than a power voltage of a digital circuit mounted on the solid-state imaging device.

8. (Previously Presented) A solid-state imaging device according to claim 4, wherein the drain transistor is off during an operation to read out the signal charge of the charge holding region on a pixel row preceding to the exposure start row.

9. (Previously Presented) A solid-state imaging device according to claim 2, wherein the transfer transistor, the reset transistor and the amplifying transistor have respective

gate wirings provided in a direction along the pixel row, to be driven on a pixel-row basis and the drain transistor has a gate wiring provided in a direction along the pixel column, the drain transistor gate wiring being short-circuited common between all the pixels at an outside of the imaging region section.

10. – 15. (Cancelled).

16. (Previously Presented) A camera apparatus for outputting an image taken by a solid-state imaging device, the camera apparatus comprising:

the solid-state imaging device having an imaging region section provided with a plurality of pixels and a processing circuit section for processing an image signal outputted from the imaging region section;

each pixel having a photoelectric converting element which generates a signal charge commensurate with a light-receiving amount;

a transfer transistor which transfers a signal charge generated by the photoelectric converting element to the charge holding region and has a threshold channel potential for turning on the transfer transistor which is set to a value higher than a potential which depletes the photoelectric converting element;

a drain transistor which drains a signal charge generated by the photoelectric converting element and has a threshold channel potential for turning on the drain transistor which is set to a value higher than a potential which depletes the photoelectric converting element; and

a charge storing region formed by a second conductivity type impurity layer in a layer beneath a charge separating region which holds a signal charge; and

a driver configuration unit which controls the transfer of signals in said device, wherein,

said driver configuration unit is configured such that after the transfer transistor simultaneously transfers the signal charge from all photoelectric converting elements to the charge holding region an exposure time of the photoelectric converting element starts while the processing unit reads the signal charge from the pixel, and

the photoelectric converting element comprises a buried photodiode having the charge separating region comprising a first conductivity type high-concentration impurity layer in an extreme surface of a semiconductor substrate.

17. (Previously Presented) A camera apparatus according to claim 16, wherein the solid-state imaging device further has a reset transistor for resetting the charge holding region with a signal charge, an amplifying transistor for outputting an electric signal corresponding to a potential on the charge holding region, and a selecting transistor for selectively activating the amplifying transistor.

18. (Cancelled).

19. (Previously Presented) A camera apparatus according to claim 16, wherein, in the solid-state imaging device, after simultaneously resetting the charge holding regions on all the pixels in the imaging region section, signal charges of the photodiodes on all the pixels are simultaneously transferred to the charge holding regions, next the signal charges transferred to the charge holding regions are read out on a pixel-row basis, to keep the drain transistor on until the reading operation proceeds to a predetermined exposure start row and drain the signal charges of the photodiodes on all the pixels, and to turn off the drain transistor when proceeded to the predetermined exposure start row and start an exposure on all the pixels.

20. (Previously Presented) A camera apparatus according to claim 19, wherein, in the solid-state imaging device, the photodiode, immediately after transferring the signal charge of the photodiode to the charge holding region by the transfer transistor, has remaining charges of 20 or less while the photodiode, immediately after draining the signal charge of the photodiode by the drain transistor, has remaining charges of 20 or less.

21. (Original) A camera apparatus according to claim 19, wherein, in the solid-state imaging device, the drain transistor being on has a gate voltage level higher than a gate voltage level of the transfer transistor being on.

22. (Original) A camera apparatus according to claim 19, wherein, in the solid-state imaging device, the drain transistor being on has a gate voltage level higher than a power voltage of a digital circuit mounted on the solid-state imaging device.

23. (Previously Presented) A camera apparatus according to claim 19, wherein, in the solid-state imaging device, the drain transistor is off during an operation to read out the signal charge of the charge holding region on a pixel row preceding to the exposure start row.

24. (Previously Presented) A camera apparatus according to claim 17, wherein, in the solid-state imaging device, the transfer transistor, the reset transistor and the amplifying transistor have respective gate wirings provided in a direction along the pixel row, to be driven on a pixel-row basis and the drain transistor has a gate wiring provided in a direction along the pixel column, the drain transistor gate wiring being short-circuited common between all the pixels at an outside of the imaging region section.

25. (Original) A camera apparatus according to claim 16, further having switch means for switching shutter operation of the solid-state imaging device between a focal-plane shutter operation and an all-the-pixel simultaneous shutter operation.

26. (Original) A camera apparatus according to claim 19, further having exposure time selecting means for selecting an exposure time of the solid-state imaging device and exposure start row selecting means for selecting the predetermined exposure start row depending upon an exposure time selected by the exposure time selecting means.

27. (Previously Presented) A solid-state imaging device comprising:  
a plurality of pixels;  
each pixel having a light-receiving part;  
a transfer transistor which reads out a charge generated in the light-receiving part and has a threshold channel potential for turning on the transfer transistor which is set to a value higher than a potential which depletes the photoelectric converting element;  
a drain transistor which drains the charge generated in the light-receiving part and has a threshold channel potential for turning on the drain transistor which is set to a value higher than a potential which depletes the photoelectric converting element; and  
a driver configuration unit which controls the transfer of signals in said device;  
a charge holding region of a second conductivity type which holds a signal charge,  
and

wherein,

    said driver configuration unit is configured such that after the transfer transistor simultaneously transfers the signal charge from all photoelectric converting elements to the charge holding region an exposure time of the photoelectric converting element starts while the processing unit reads the signal charge from the pixel, and

    the light-receiving part has a charge storing region with a potential increasing as the stored charge decreases during reading out charges and during draining charges but lower than a potential on a channel part in a state the transfer transistor is on and a potential on the channel part in a state the drain transistor is on when the charge storing region is substantially depleted.

28. (Original) A solid-state imaging device according to claim 27, wherein the charge storing region when substantially depleted includes charges (electrons or charges) in the number of 20 or less.

29. (Original) A solid-state imaging device according to claim 27, wherein the pixel further has a charge holding part for holding a charge read out by the transfer transistor,

    the charge stored in the charge storing region being to be read out, simultaneously on all the pixels, to the charge holding part by the transfer transistor included in each of the plurality of pixels,

    the charge held at the charge holding part included in each of the plurality of pixels being to be read out as a pixel signal in a predetermined order to an external of the pixel,

    the plurality of pixels, in a time period the pixel signal is being read out, being drained of an unwanted charge in the charge storing region by the drain transistors, thereby staring an exposure time period.

30. (Previously Presented) A solid-state imaging device comprising:  
    a plurality of pixels;  
    each pixel having a light-receiving part ;  
    a transfer transistor which reads out a charge in a manner substantially depleting a charge storing region included in the light-receiving part which has a threshold channel potential for

turning on the transfer transistor which is set to a value higher than a potential which depletes the light-receiving part;

    a drain transistor which has a threshold channel potential for turning on the drain transistor which is set to a value higher than a potential which depletes the light-receiving part; and

    a driver configuration unit which controls the transfer of signals in said device; a charge holding region of a second conductivity type which holds a signal charge,

and

    wherein,

    said driver configuration unit is configured such that after the transfer transistor simultaneously transfers the signal charge from all photoelectric converting elements to the charge holding region an exposure time of the photoelectric converting element starts while the processing unit reads the signal charge from the pixel, and

    a potential on a channel part in a state the drain transistor is on is higher than a potential on a channel part in a state the transfer transistor is on.

31. (Original) A solid-state imaging device according to claim 30, wherein the charge storing region when substantially depleted includes charges (electrons or charges) in the number of 20 or less.

32. (Previously Presented) A solid-state imaging device having an imaging region section provided with a plurality of pixels and a processing circuit section for processing an image signal outputted from the imaging region section, the solid-state imaging device comprising:

    each pixel having a photoelectric converting element for generating a signal charge commensurate with a light-receiving amount;

    a charge holding region of a second conductivity type which holds a signal charge; a transfer transistor which transfers a signal charge generated by the photoelectric converting element to the charge holding region and has a threshold channel potential for turning on the transfer transistor which is set to a value higher than a potential which depletes the light-receiving part;

a drain transistor which drains a signal charge generated by the photoelectric converting element and has a threshold channel potential for turning on the drain transistor which is set to a value higher than a potential which depletes the light-receiving part;

a reset transistor which resets the charge holding region with a signal charge, an amplifying transistor which outputs an electric signal corresponding to a potential on the charge holding region, and a selecting transistor which selectively activates the amplifying transistor; and

a driver configuration unit which controls the transfer of signals in said device, and wherein,

said driver configuration unit is configured such that after the transfer transistor simultaneously transfers the signal charge from all photoelectric converting elements to the charge holding region an exposure time of the photoelectric converting element starts while the processing unit reads the signal charge from the pixel, and

the photoelectric converting element comprises a buried photodiode having a charge separating region comprising a first conductivity type high-concentration impurity layer in an extreme surface of a semiconductor substrate and a charge storing region comprising a second conductivity type impurity layer in a layer beneath the charge separating region, and

after simultaneously resetting the charge holding regions on all the pixels in the imaging region section, signal charges of the photodiodes on all the pixels are simultaneously transferred to the charge holding regions, next the signal charges transferred to the charge holding regions are read out on a pixel-row basis, to keep the drain transistor on until the reading operation proceeds to a predetermined exposure start row and drain the signal charges of the photodiodes on all the pixels.

33. (Previously Presented) A solid-state imaging device having an imaging region section provided with a plurality of pixels and a processing circuit section for processing an image signal outputted from the imaging region section, the solid-state imaging device comprising:

each pixel having a photoelectric converting element which generates a signal charge commensurate with a light-receiving amount;

a charge holding region of a second conductivity type which holds a signal charge;

a transfer transistor which transfers a signal charge generated by the photoelectric converting element to the charge holding region and has a threshold channel potential for turning on the transfer transistor which is set to a value higher than a potential which depletes the light-receiving part;

a drain transistor which drains a signal charge generated by the photoelectric converting element and has a threshold channel potential for turning on the drain transistor which is set to a value higher than a potential which depletes the light-receiving part;

a reset transistor which resets the charge holding region with a signal charge, an amplifying transistor which outputs an electric signal corresponding to a potential on the charge holding region, and a selecting transistor which selectively activates the amplifying transistor; and

a driver configuration unit which controls the transfer of signals in said device, and wherein,

said driver configuration unit is configured such that after the transfer transistor simultaneously transfers the signal charge from all photoelectric converting elements to the charge holding region an exposure time of the photoelectric converting element starts while the processing unit reads the signal charge from the pixel, and

the photoelectric converting element comprises a buried photodiode having a charge separating region comprising a first conductivity type high-concentration impurity layer in an extreme surface of a semiconductor substrate and a charge storing region comprising a second conductivity type impurity layer in a layer beneath the charge separating region,

after simultaneously resetting the charge holding regions on all the pixels in the imaging region section, signal charges of the photodiodes on all the pixels are simultaneously transferred to the charge holding regions, next the signal charges transferred to the charge holding regions are read out on a pixel-row basis, to keep the drain transistor on until the reading operation proceeds to a predetermined exposure start row and drain the signal charges of the photodiodes on all the pixels, and

the drain transistor is off during an operation to read out the signal charge of the charge holding region on a pixel row preceding to the exposure start row.